

FIG. 1

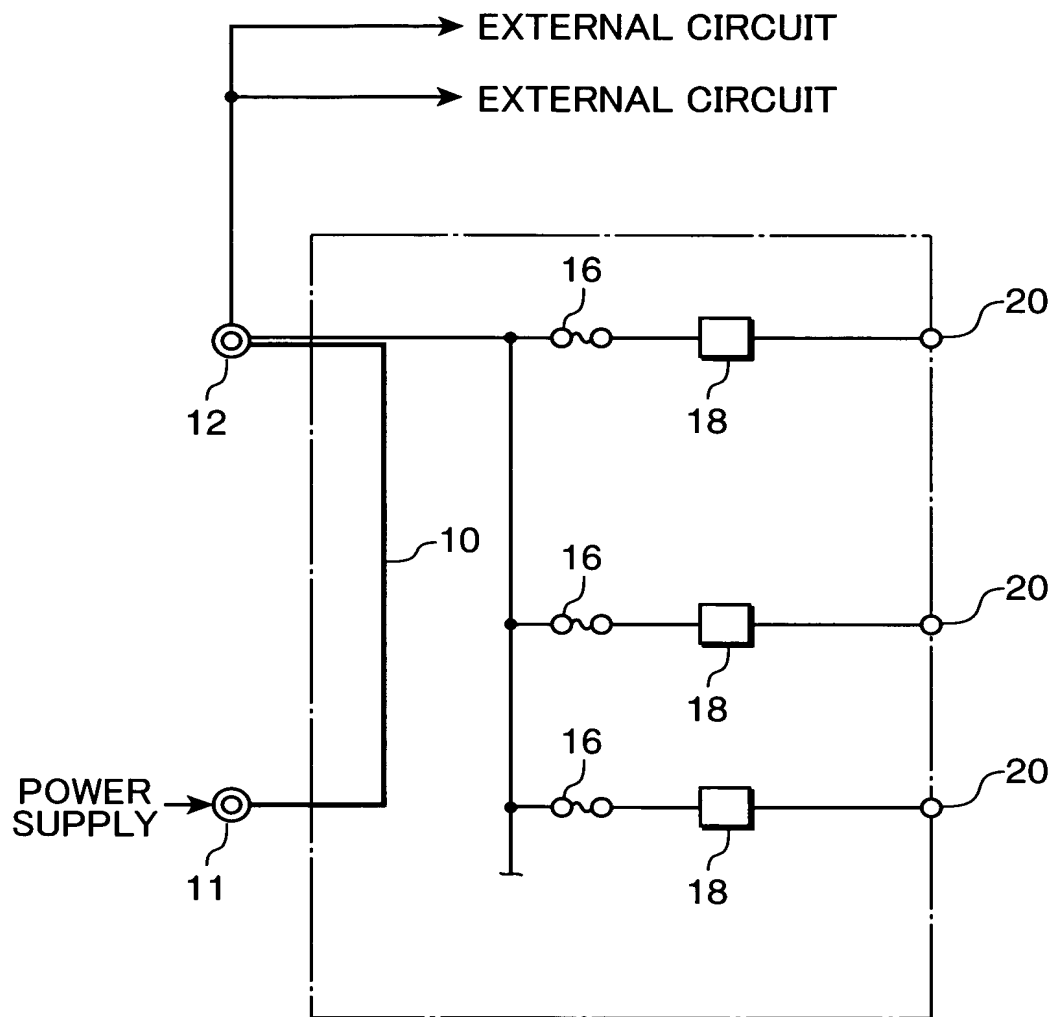
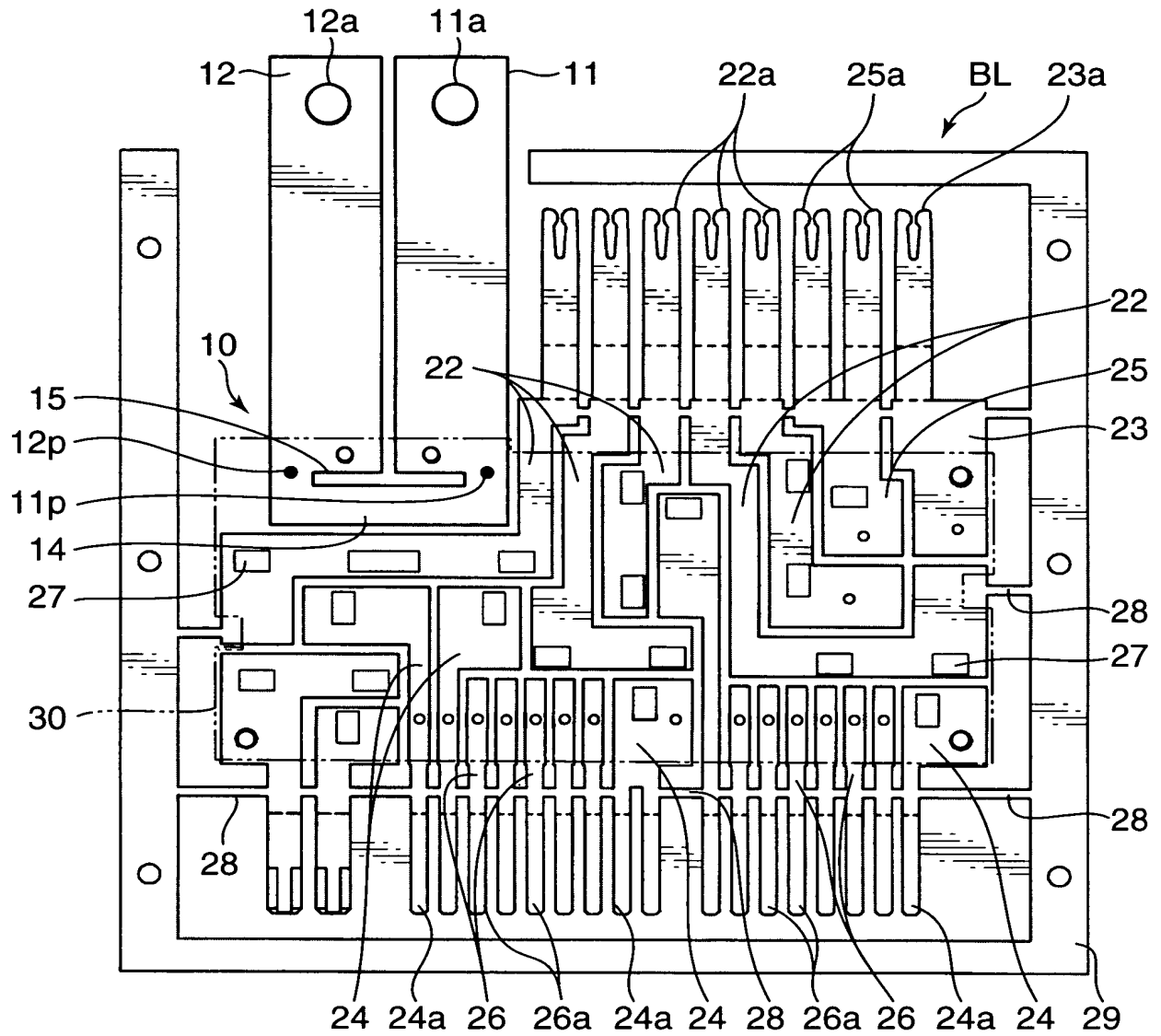


FIG. 2



A cross-sectional view of a semiconductor device. A substrate 11(12) is shown at the bottom. A gate stack 25 is formed on the substrate, consisting of a gate electrode 25a and a gate insulating layer BL. A channel layer 30 is formed on the gate stack.

FIG. 4A

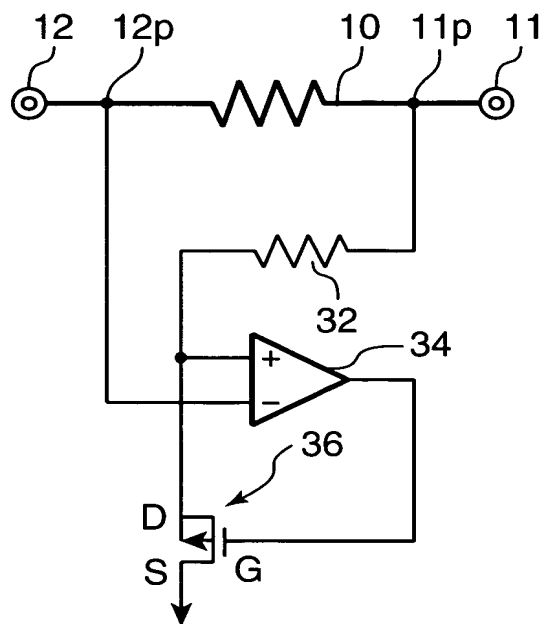


FIG. 4B

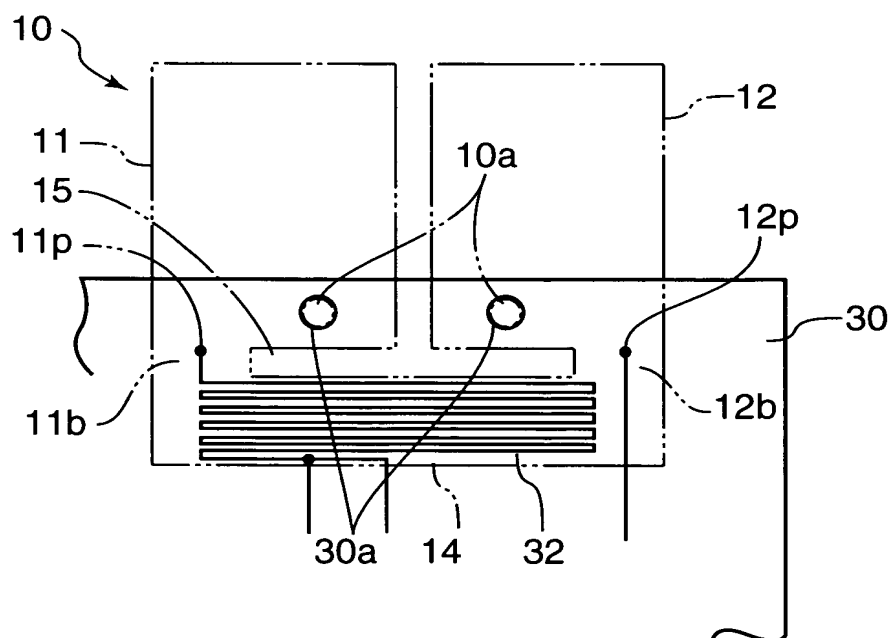


FIG. 5A

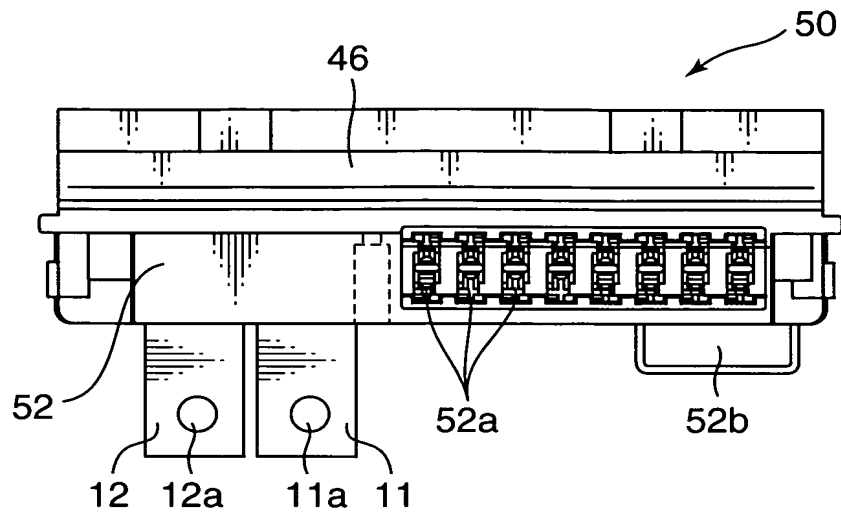


FIG. 5B

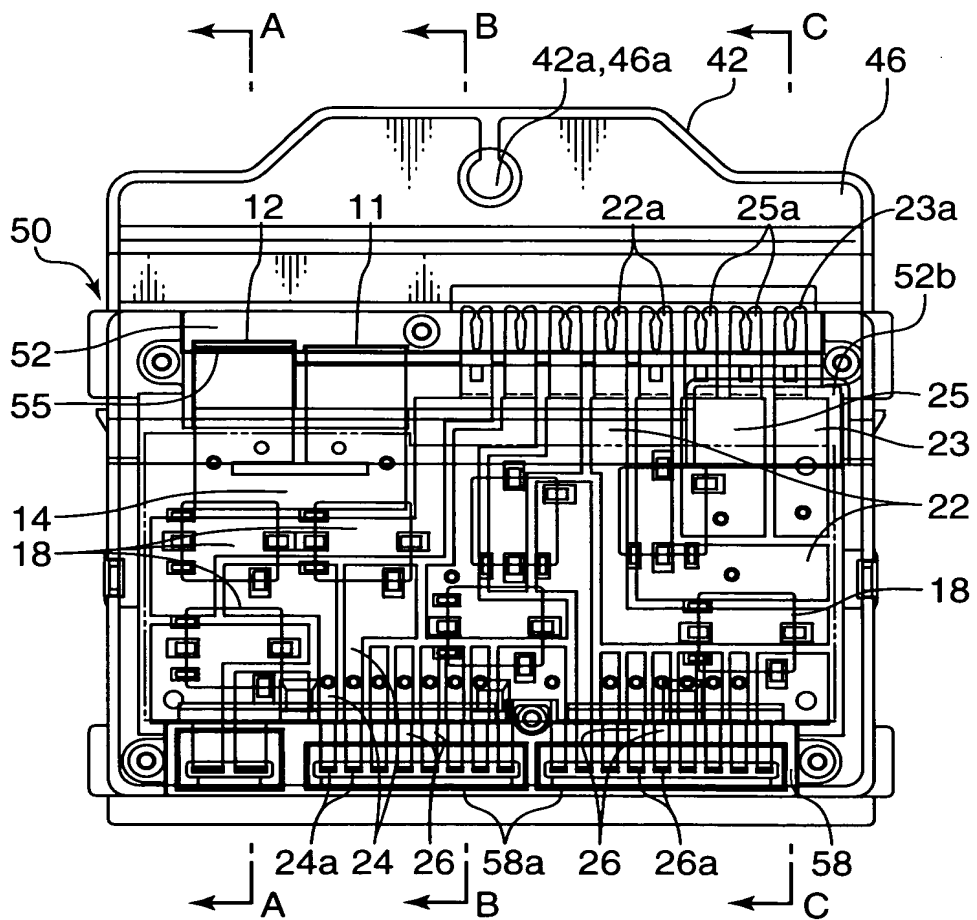


FIG. 6C

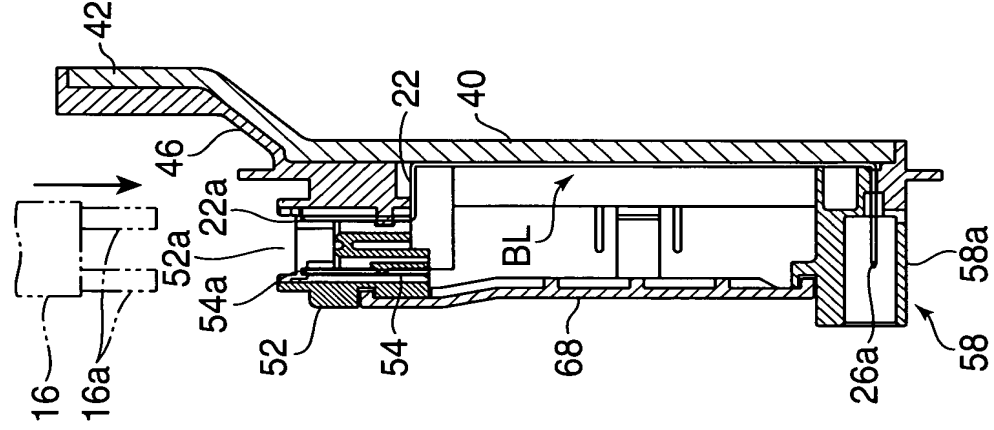


FIG. 6C

FIG. 7A

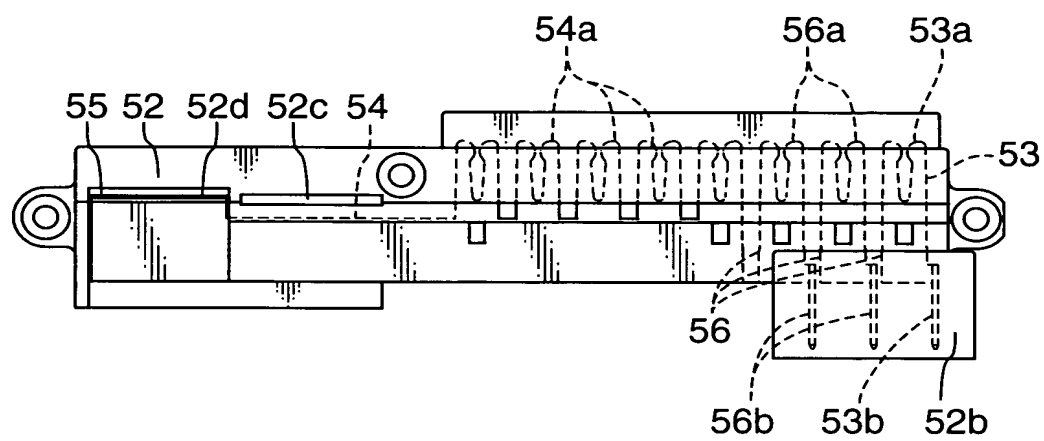


FIG. 7B

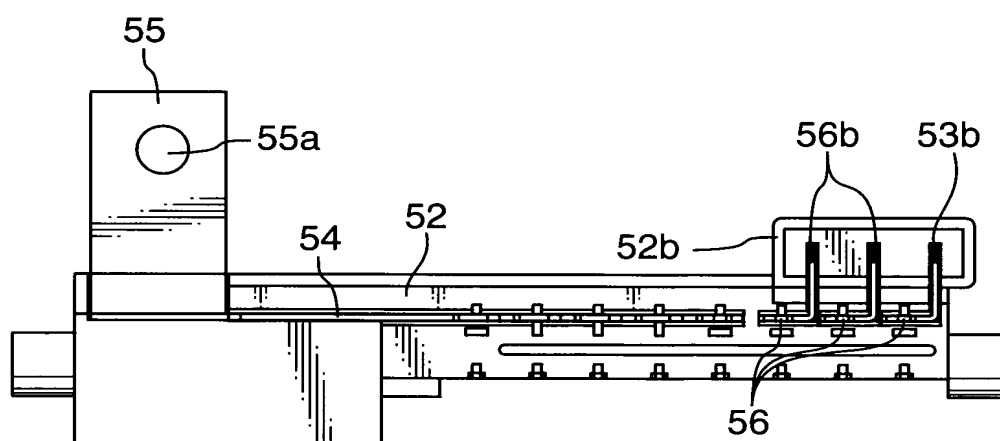


FIG. 8

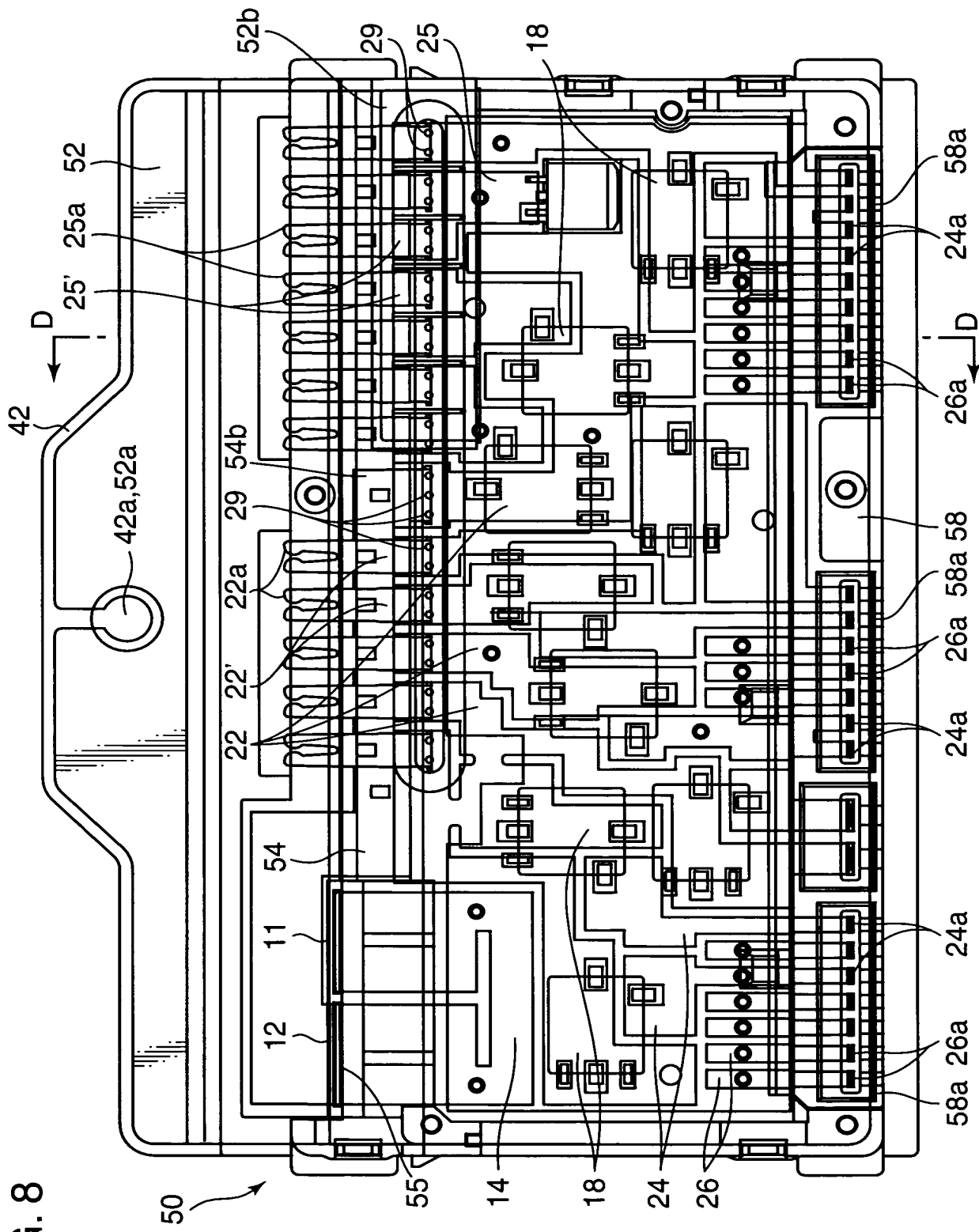




FIG. 9

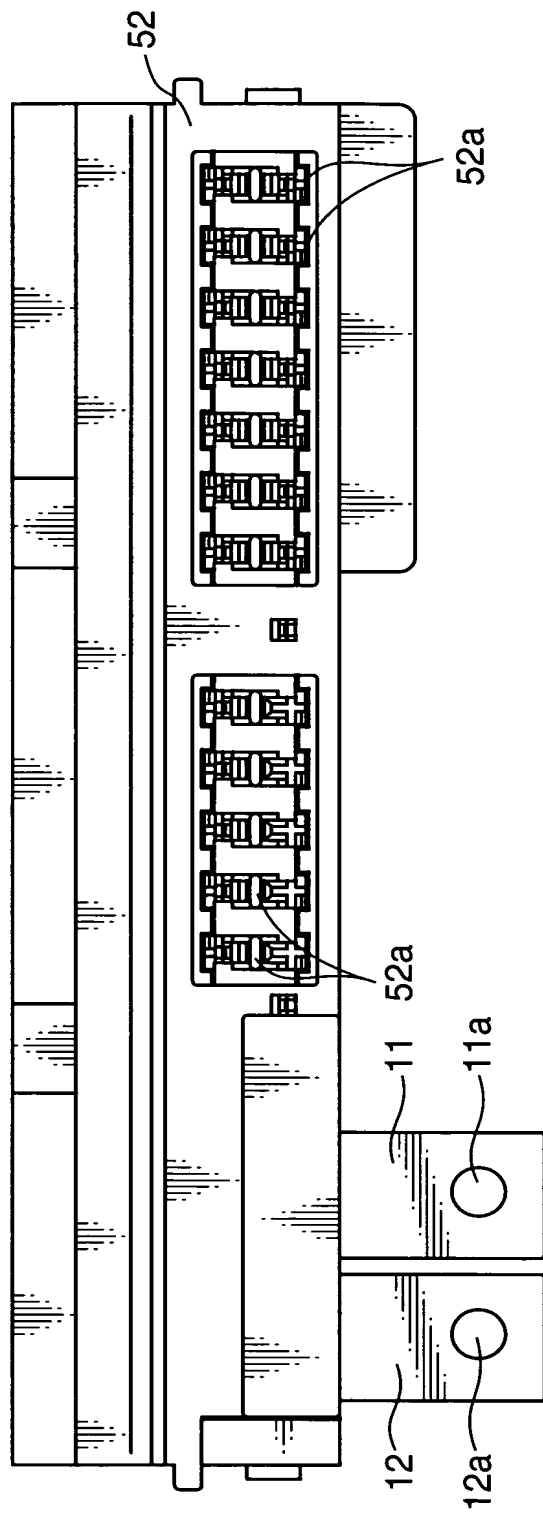


FIG.10

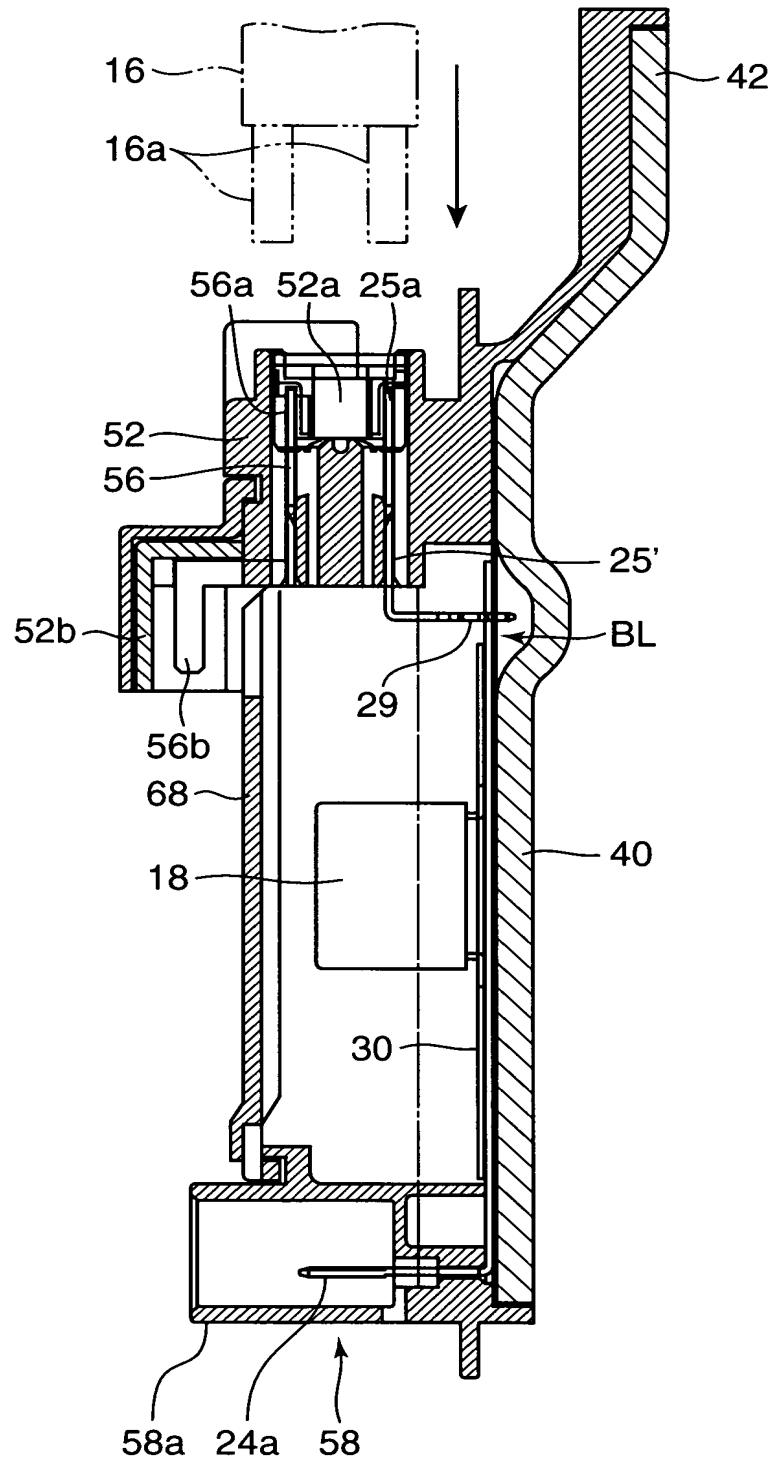


FIG. 11A

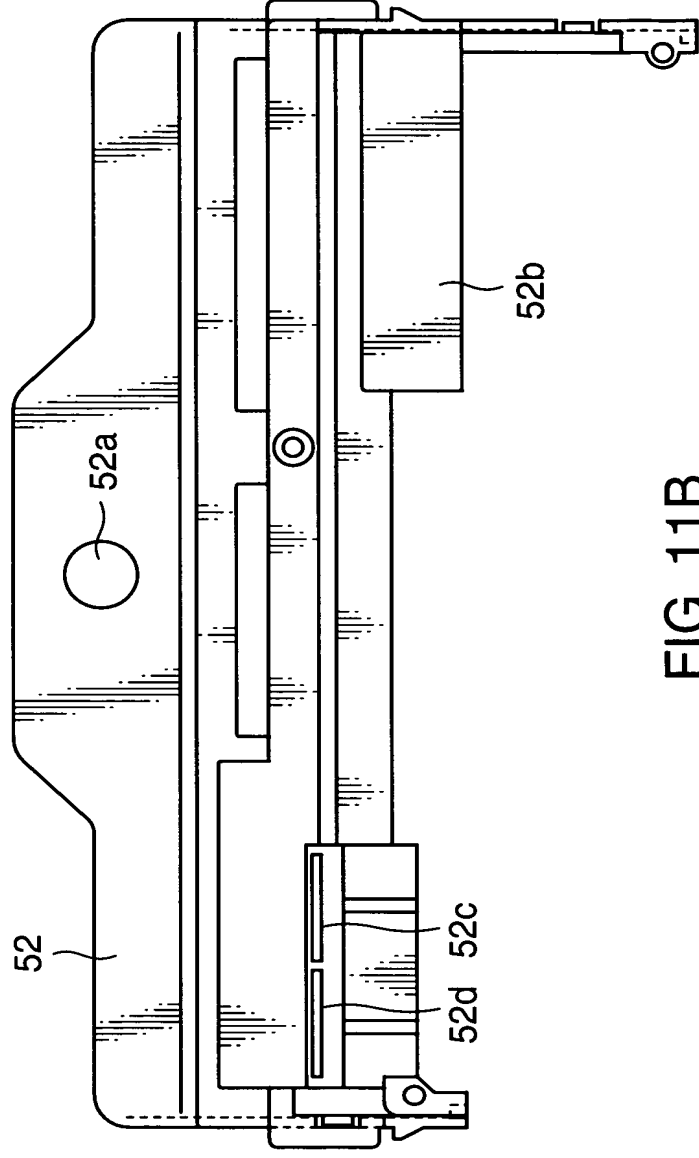


FIG. 11B

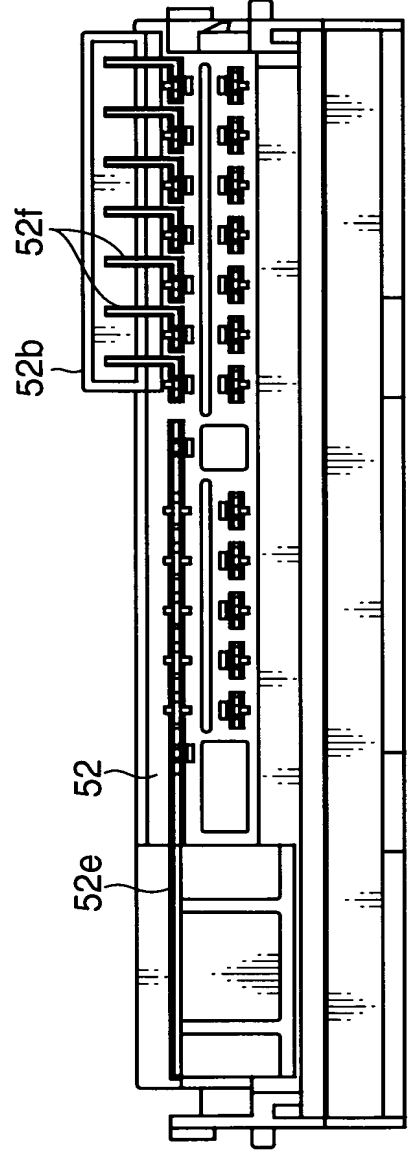


FIG. 12A

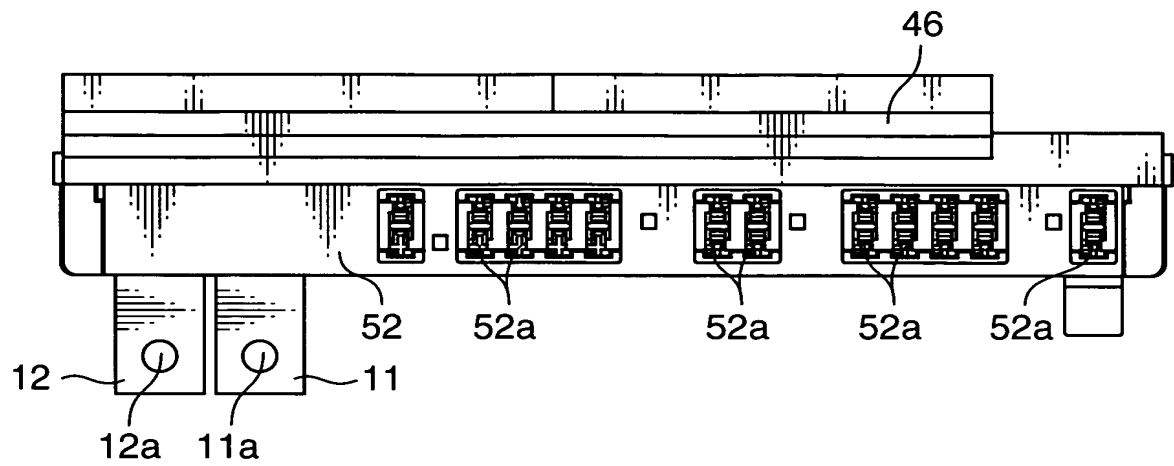


FIG. 12B

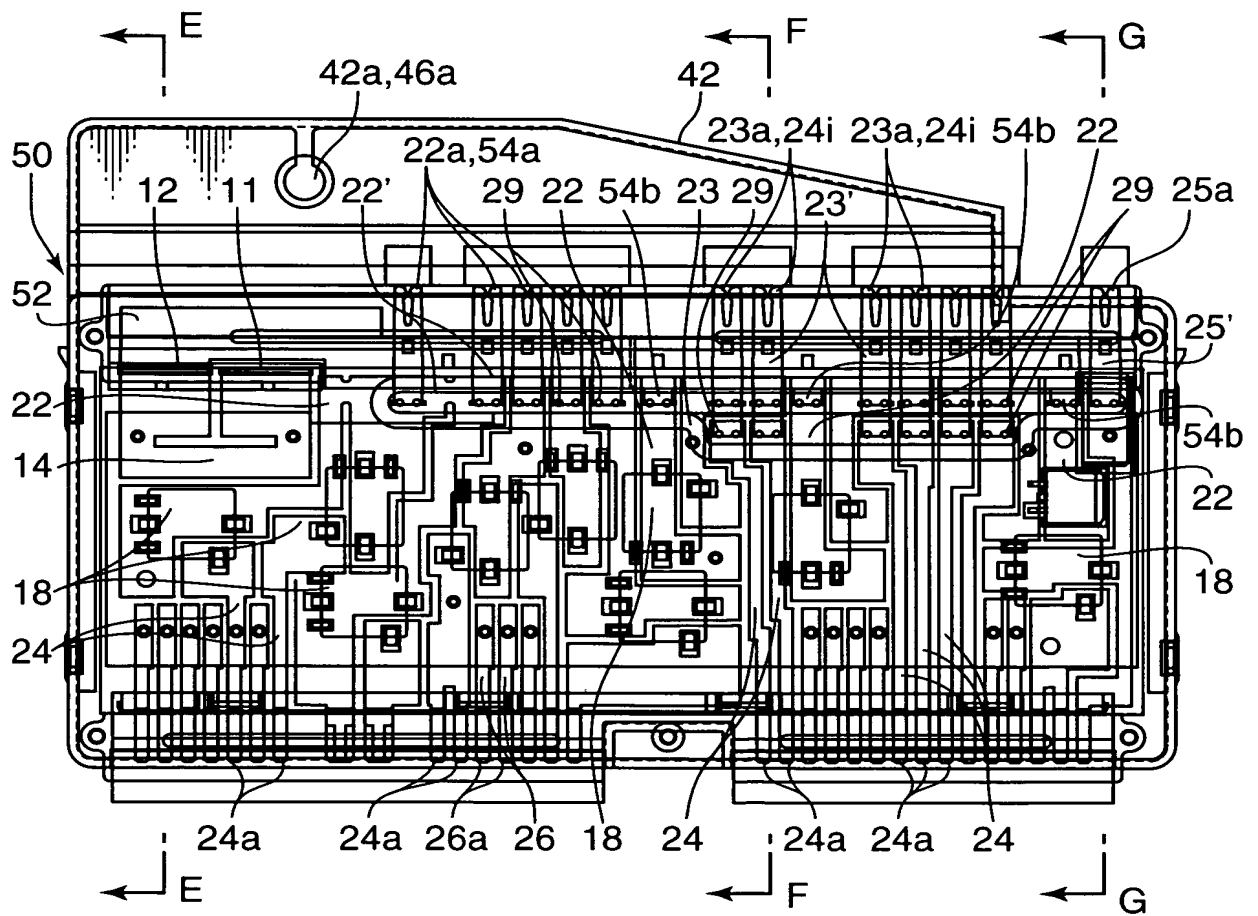


FIG. 13A

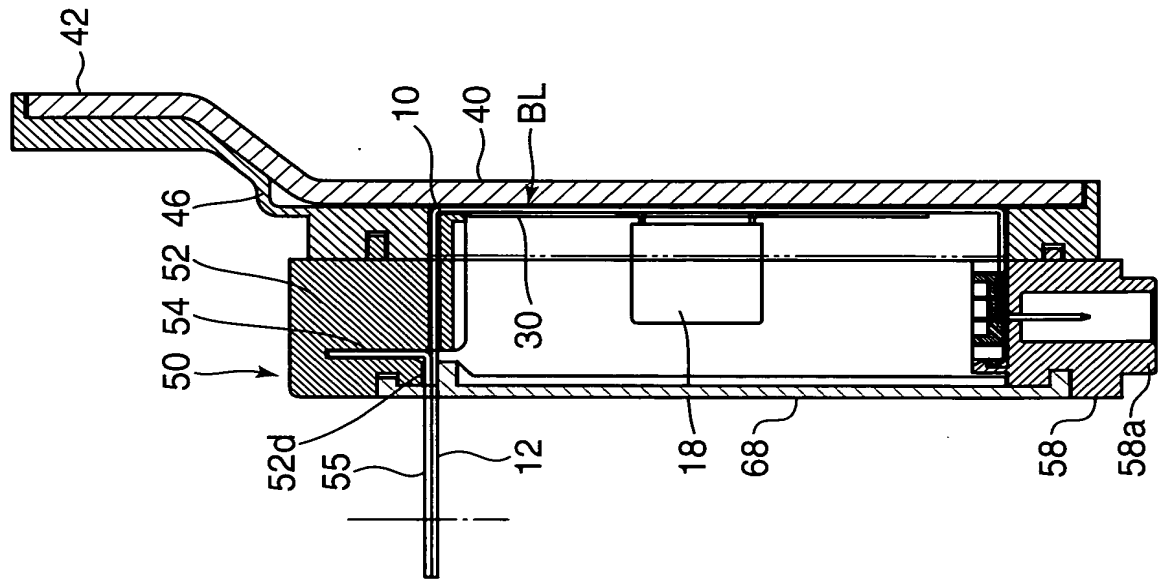


FIG. 13B

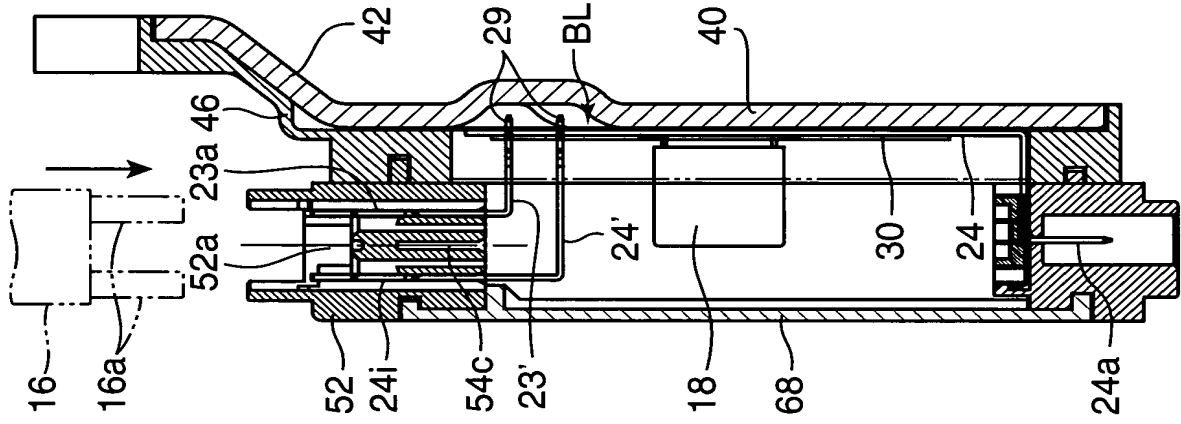


FIG. 13C

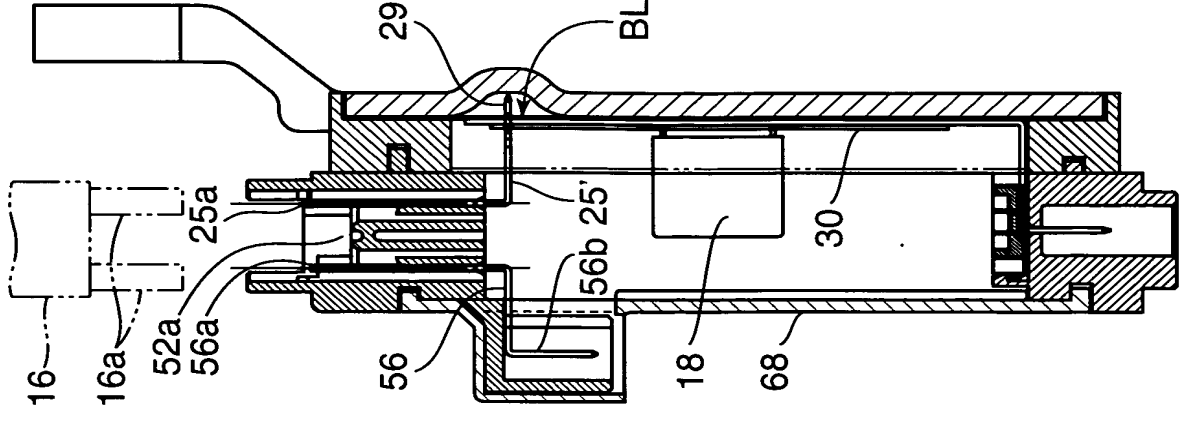


FIG. 14A

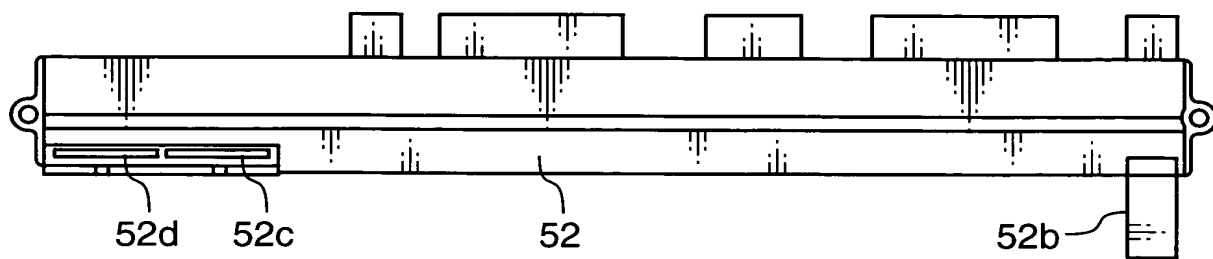


FIG. 14B

